### FL5252050R

## **Panasonic**

### FL5252050R

Silicon P-channel MOSFET(FET) Silicon epitaxial planar type(SBD)

For switching For DC-DC Converter

#### ■ Features

- Low drain-source ON resistance : RDS (on) typ. = 100 m $\Omega$  ( VGS = -4.0 V )
- Low drive voltage: 2.5 V drive
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol : Y0

Established: 2011-06-17

: 2013-10-28

Revised

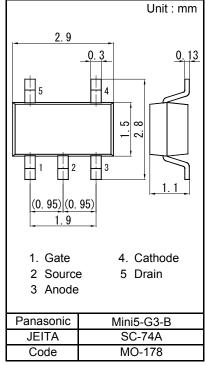
#### ■ Packaging

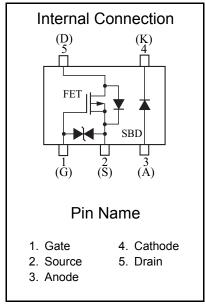
Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

項目		Symbol	Rating	Unit	
FET	Drain to Source Voltage	VDS	-20	V	
	Gate to Source Voltage	VGS	±10	V	
	Drain current	ID	-2.1	Α	
	Drain Current (Pulsed)	IDp	-8	Α	
	Channel temperature	Tch	125	°C	
SBD	Reverse voltage	VR	20	V	
	Forward current (Average)	IF(AV)	700	mA	
	Junction temperature	Tj	125	°C	
Overall	Total power dissipation *1	PD	600	mW	
	Operating ambient temperature	Topr	-40 to + 85	°C	
	Storage temperature	Tstg	-55 to +125	°C	

Note: \*1 Measuring on ceramic substrate at 40 mm × 38 mm × 0.1 mm
PD absolute maximum rating without a heat shink: 300 mW





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■ Electrical Characteristics Ta = 25 °C ± 3 °C FET (P-ch.)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain to Source Breakdown Voltage	VDSS	ID = -1 mA, VGS = 0	-20			V
Zero Gate Voltage Drain Current	IDSS	VDS = -20 V, VGS = 0			-1.0	μA
Gate-source Leakage Current	IGSS	$VGS = \pm 8 \text{ V}, VDS = 0$			±10	μA
Gate-source Threshold Voltage	Vth	ID = -1.0 mA, VDS = -10 V	-0.4	-0.85	-1.3	V
Drain-source On-State Resistance	RDS(on)1	ID = -1.0 A, VGS = -4.0 V		100	130	mΩ
Dialii-source Oil-State Resistance	RDS(on)2	ID = -0.5 A, VGS = -2.5 V		130	200	
Forward transfer admittance	Yfs	ID = -1.0 A, VDS = -10 V	3.0			S
Input Capacitance	Ciss			400		pF
Output Capacitance	Coss	VDS = -10 V, $VGS = 0$ , $f = 1 MHz$		40		pF
Reverse Transfer Capacitance	Crss			35		pF
Turn-on time <sup>*1</sup>	ton	VDD = -10 V, VGS = 0 to -4 V	35		ne	
rum-on time		ID = -1.0 A	35			ns
Turn-off time <sup>*1</sup>	toff	VDD = -10 V, VGS = -4 to 0 V		100		no
Turn-on time		ID = -1.0 A	100		ns	

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

#### **SBD**

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	VF	IF = 700 mA			0.45	V
Reverse current	IR	VR = 20 V			200	μA
Terminal capacitance	Ct	VR = 10 V, f = 1 MHz		12		pF
Reverse recovery time	trr	IF = IR = 100 mA, Irr = 10 mA		4.3		ns

Note: Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for diodes.

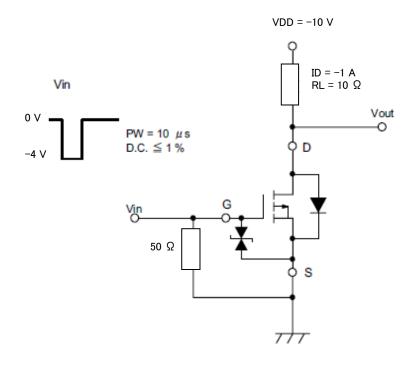
Established: 2011-06-17 : 2013-10-28 Revised

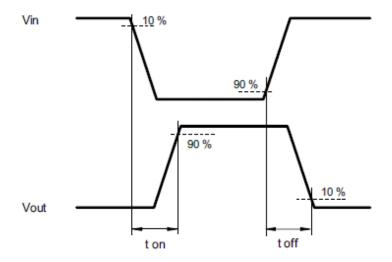
<sup>2. \*1</sup> Turn-on, Turn-off measurement circuit

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\*1 Turn-on, Turn-off measurement circuit





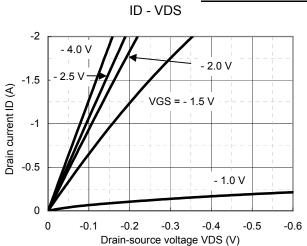
Revision. 3

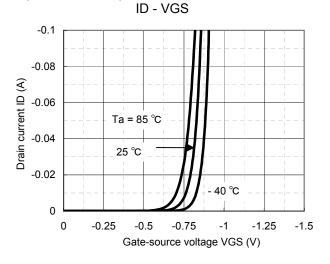
MOS FET

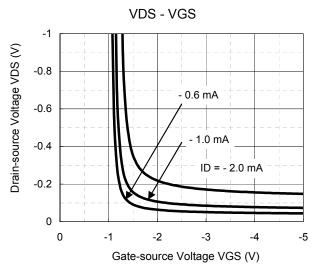
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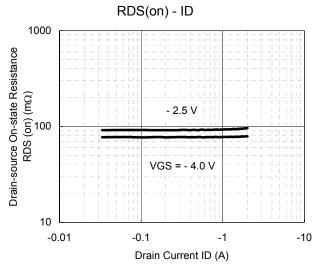
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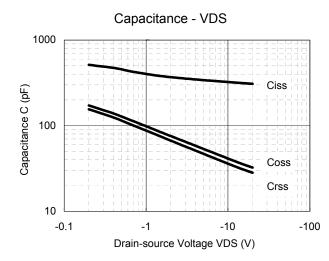
### Technical Data (reference)









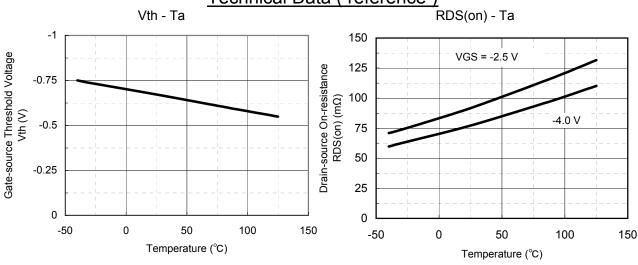


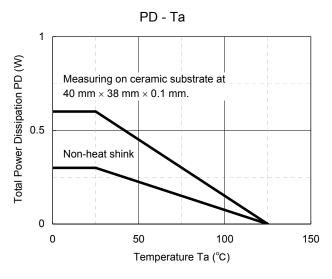
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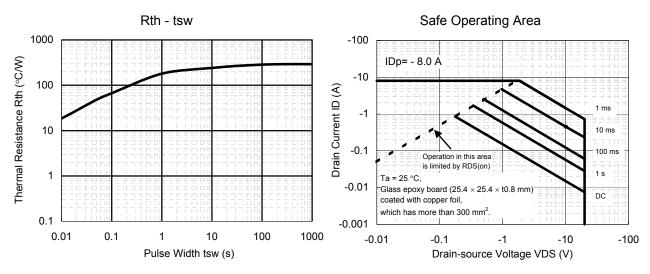
MOS FET

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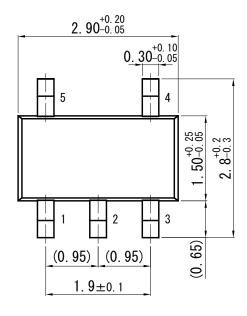


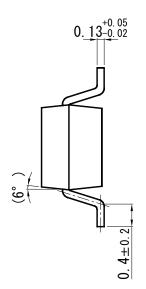
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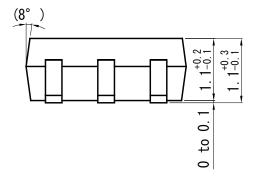
## Mini5-G3-B

**Panasonic** 

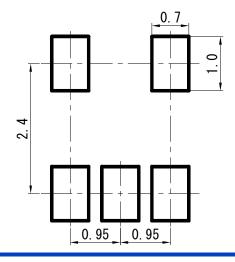
Unit: mm







### ■ Land Pattern (Reference) (Unit: mm)



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